



80V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max T _C = +25°C	
	7mΩ @ V _{GS} = 10V	68A	
80V	10.5mΩ @ V _{GS} = 6V	56A	

Description

This MOSFET is designed to minimize the on-state resistance (RDS(ON)) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

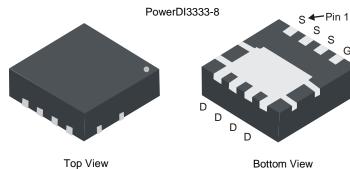
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

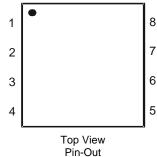
Features and Benefits

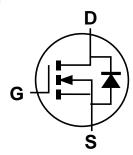
- Rated to +175°C Ideal for High Ambient Temperature **Environments**
- Low RDS(ON) Ensures On-State Losses are Minimized
- Excellent Qgd x RDS(ON) Product (FOM)
- Advanced Technology for DC-DC Converts
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.072 grams (Approximate)







Equivalent Circuit

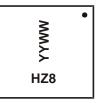
Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH8008SFG-7	PowerDI3333-8	2,000/Tape & Reel
DMTH8008SFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain < 900ppm bromine, < 900ppm chlorine (< 1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



HZ8 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	80	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current (Note 7) V _{GS} = 10V	T _C = +25°C T _C = +100°C	lD	68 48	А
Continuous Drain Current (Note 6) V _{GS} = 10V	ID	17 12	А	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	68	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	272	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1	I _{SM}	272	Α	
Avalanche Current, L = 1mH (Note 8)	las	18.7	Α	
Avalanche Energy, L = 1mH (Note 8)	Eas	174.85	mJ	

Thermal Characteristics

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	P_{D}	1.2	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	125	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	46	°C/W
Total Power Dissipation (Note 7)	T _C = +25°C	Pp	50	W
Thermal Resistance, Junction to Case (Note 7)		R _θ JC	3.0	°C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +175	°C

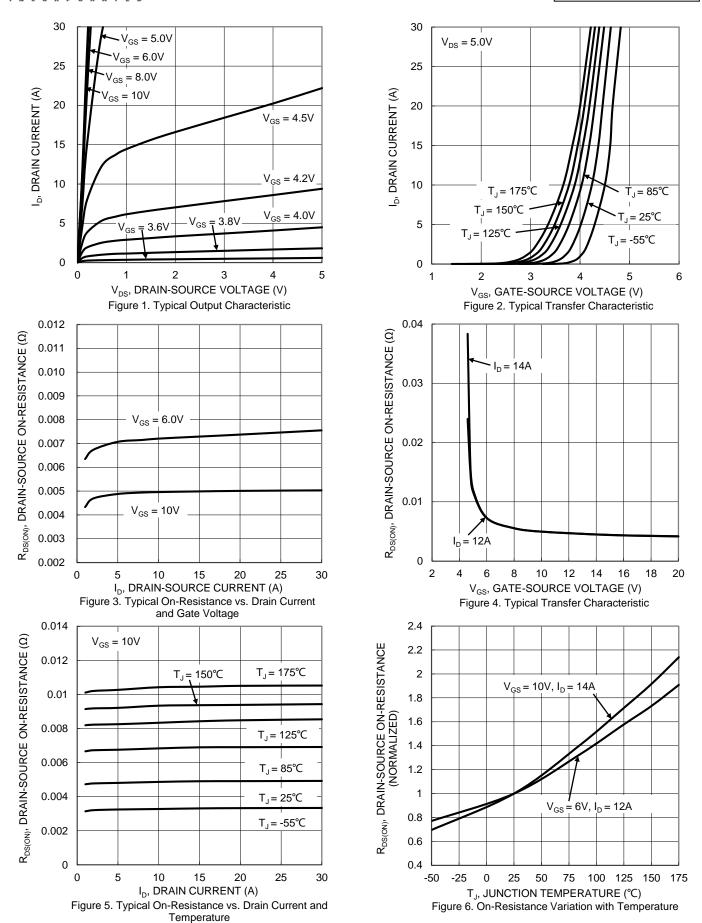
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Drain-Source Breakdown Voltage	BV _{DSS}	80	-	_	$V = V_{GS} = 0V, I_D = 1mA$		
Zero Gate Voltage Drain Current	IDSS	-	l	1	μA V _{DS} = 64V, V _{GS} = 0V		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)						•	
Gate Threshold Voltage	Vgs(TH)	2		4	V	$V_{DS} = V_{GS}$, $I_D = 1mA$	
Static Drain-Source On-Resistance			5.0	7	mΩ	V _{GS} = 10V, I _D = 14A	
Static Dialii-Source Off-Resistance	RDS(ON)	_	7.1	10.5		V _G S = 6V, I _D = 12A	
Diode Forward Voltage	V _{SD}	_	0.8	1.2	V	V _{GS} = 0V, I _S = 14A	
DYNAMIC CHARACTERISTICS (Note 10)						•	
Input Capacitance	Ciss	_	1945	_		V _{DS} = 40V, V _{GS} = 0V, f = 1MHz	
Output Capacitance	Coss	_	750	_	pF		
Reverse Transfer Capacitance	Crss	_	45.8	_			
Gate Resistance	Rg	_	1.8	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 5V)	Qg	_	18.4	_			
Total Gate Charge (V _{GS} = 10V)	Qg	_	31.7	_	nC	V _{DS} = 40V, I _D = 14A	
Gate-Source Charge	Qgs	_	8.3	_	nc		
Gate-Drain Charge	Qgd	_	8.6	_			
Turn-On Delay Time	t _{D(ON)}	_	9.2	_		$V_{DD} = 40V, V_{GS} = 10V,$ $I_{D} = 14A, R_{G} = 6\Omega$	
Turn-On Rise Time	t _R	_	11.8	_			
Turn-Off Delay Time	tD(OFF)	_	27.0	_	ns		
Turn-Off Fall Time	tF	_	17.3	_			
Body Diode Reverse Recovery Time	trr	_	40.6	_	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	_	50.9	_	nC	$\frac{1}{100}$ Is = 14A, di/dt = 100A/µs	

Notes:

- 5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
- 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
- 9. Short duration pulse test used to minimize self-heating effect.
- 10. Guaranteed by design. Not subject to product testing.









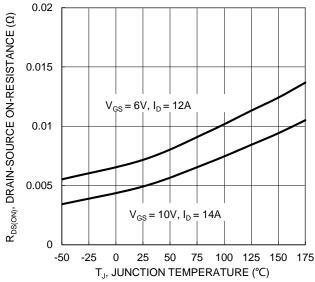


Figure 7. On-Resistance Variation with Temperature

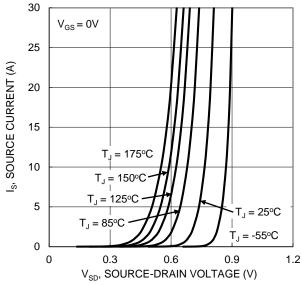


Figure 9. Diode Forward Voltage vs. Current

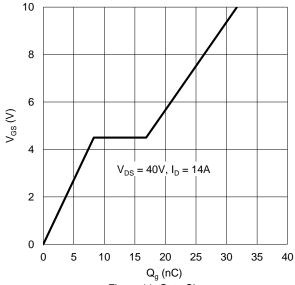


Figure 11. Gate Charge

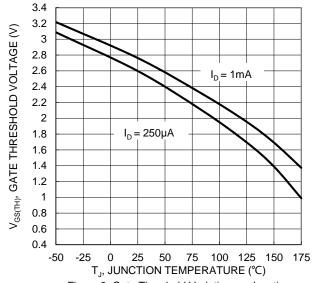
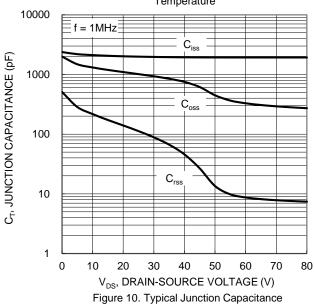


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 $R_{DS(ON)}$ 100 ID, DRAIN CURRENT (A) 10 = 10 msT_C = 25°C Single Pulse $P_{W} = 100 \text{ms}$ DUT on Infinite Heatsink $V_{GS} = 10V$ 0.01 1000 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V) Figure 12. SOA, Safe Operation Area



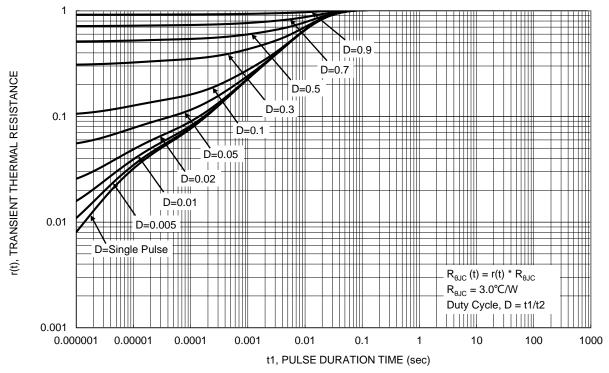


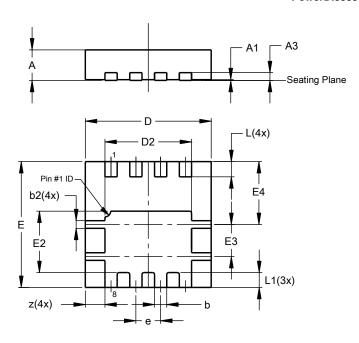
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8

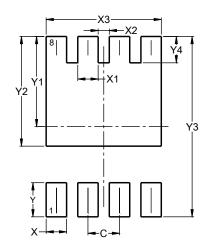


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
A3	-	_	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
Е	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	0.6		0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
z	_	_	0.515		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



Dimensions	Value (in mm)		
С	0.650		
Х	0.420		
X1	0.420		
X2	0.230		
Х3	2.370		
Υ	0.700		
Y1	1.850		
Y2	2.250		
Y3	3.700		
Y4	0.540		



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